

Enhancement Mode N-Channel Power MOSFET

Features

- ◆ Low $R_{DS(on)}$ & FOM
- ◆ Extremely low switching loss
- ◆ Excellent stability and uniformity
- ◆ Easy to drive

Applications

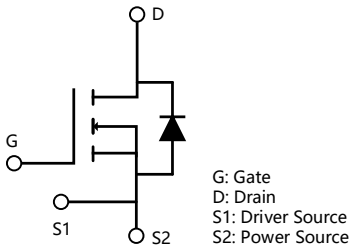
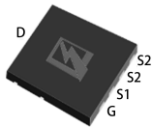
- ◆ Lighting
- ◆ Hard switching PWM
- ◆ Server power supply
- ◆ Charger

■ General Description

OSG60R150JF uses advanced GreenMOS™ technology to provide low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. This device is suitable for active power factor correction and switching mode power supply applications.

◆ $V_{DS, min@Tjmax}$	650 V
◆ $I_D, pulse$	69 A
◆ $R_{DS(ON), max @ V_{GS}=10 V}$	150 mΩ
◆ Q_g	23 nC

■ Schematic and Package Information

SCHEMATIC DIAGRAM	PIN ASSIGNMENT-TOP VIEW
 <p>G: Gate D: Drain S1: Driver Source S2: Power Source</p>	 <p>PDFN8×8 OSG60R150JF</p>

■ Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	600	V
Gate source voltage	V_{GS}	±30	V
Continuous drain current ¹⁾ , $T_C=25^\circ\text{C}$	I_D	23	A
Continuous drain current ¹⁾ , $T_C=100^\circ\text{C}$		14.5	
Pulsed drain current ²⁾ , $T_C=25^\circ\text{C}$	$I_{D, pulse}$	69	A
Power dissipation ³⁾ , $T_C=25^\circ\text{C}$	P_D	151	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	600	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots480\text{ V}$, $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

■ Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.82	$^{\circ}\text{C}/\text{W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^{\circ}\text{C}/\text{W}$

■ Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	600			V	$V_{GS}=0\text{ V}$, $I_D=250\ \mu\text{A}$
		650	716			$V_{GS}=0\text{ V}$, $I_D=250\ \mu\text{A}$, $T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2.9		3.9	V	$V_{DS}=V_{GS}$, $I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		0.12	0.15	Ω	$V_{GS}=10\text{ V}$, $I_D=10\text{ A}$
			0.29			$V_{GS}=10\text{ V}$, $I_D=10\text{ A}$, $T_j=150^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$

■ Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		1356		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}		155		pF	
Reverse transfer capacitance	C_{rss}		2		pF	
Turn-on delay time	$t_{d(on)}$		38.2		ns	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $R_G=25\ \Omega$, $I_D=10\text{ A}$
Rise time	t_r		25.2		ns	
Turn-off delay time	$t_{d(off)}$		79.2		ns	
Fall time	t_f		31.5		ns	

■ Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		23		nC	$I_D=10\text{ A}$, $V_{DS}=400\text{ V}$, $V_{GS}=10\text{ V}$
Gate-source charge	Q_{gs}		6.0		nC	
Gate-drain charge	Q_{gd}		8.3		nC	
Gate plateau voltage	V_{plateau}		5.6		V	

■ Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward current	I_S			23	A	$V_{GS} < V_{th}$
Pulsed source current	I_{SP}			69		
Diode forward voltage	V_{SD}			1.4	V	$I_S=23\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		258.1		ns	$V_R=400\text{ V}$, $I_S=10\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		2.8		μC	
Peak reverse recovery current	I_{rrm}		19		A	

■ Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=100\text{ V}$, $R_G=25\text{ }\Omega$, $L=10.8\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

■ **Electrical Characteristics Diagrams**

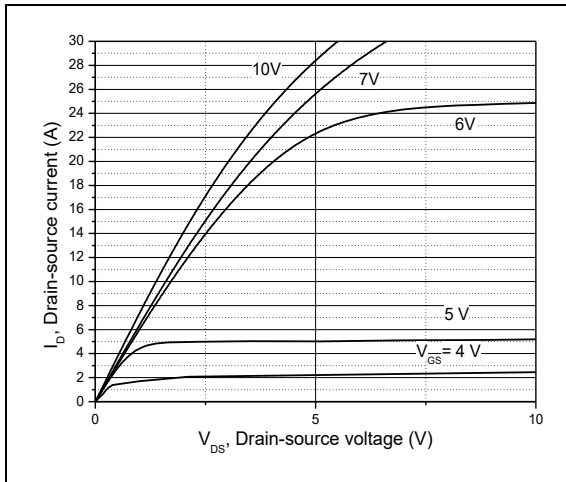


Figure 1, Typ. output characteristics

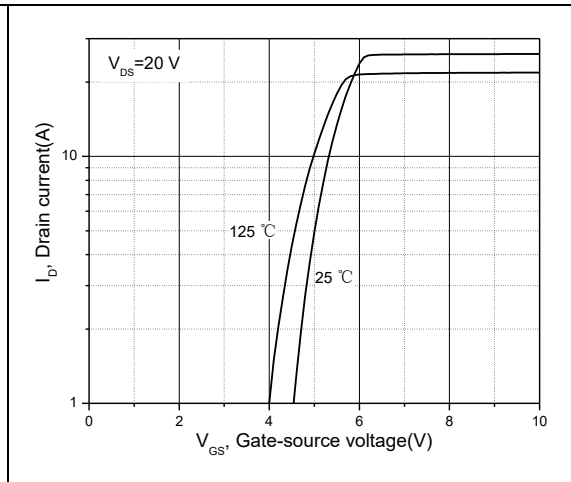


Figure 2, Typ. transfer characteristics

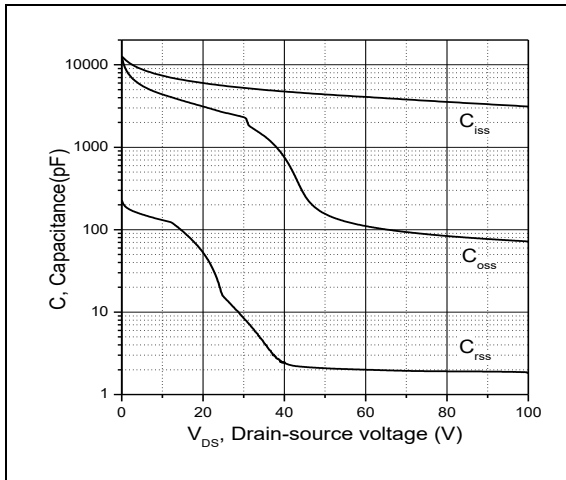


Figure 3, Typ. capacitances

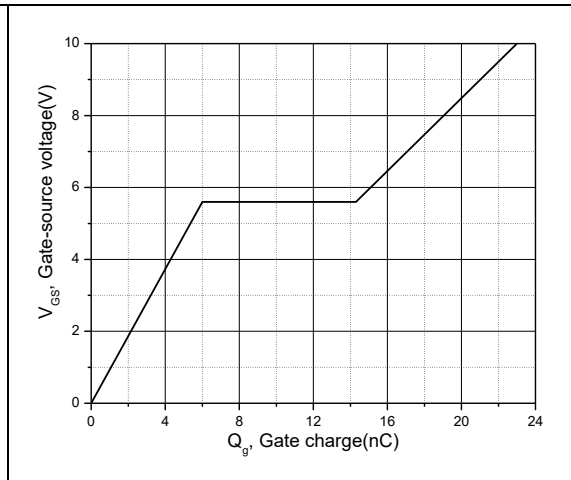


Figure 4, Typ. gate charge

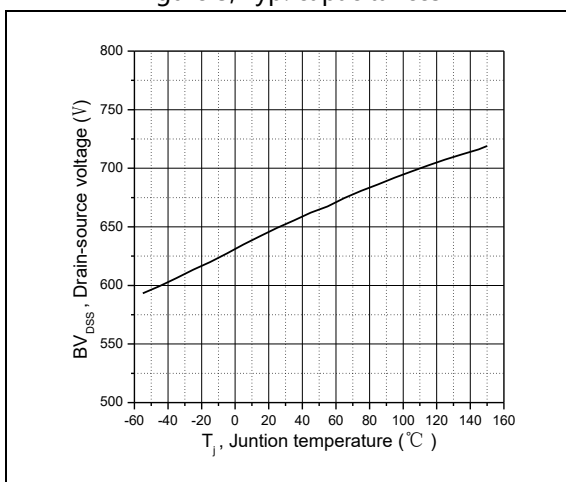


Figure 5, Drain-source breakdown voltage

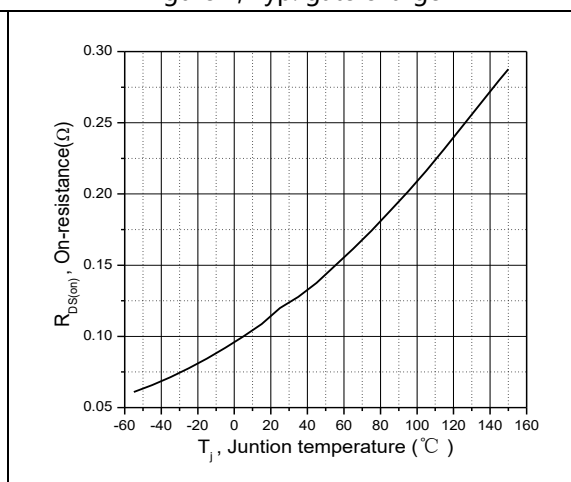


Figure 6, Drain-source on-state resistance

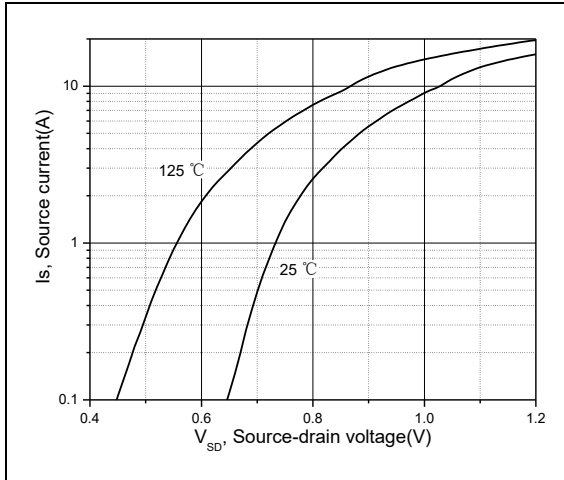


Figure 7, Forward characteristic of body diode

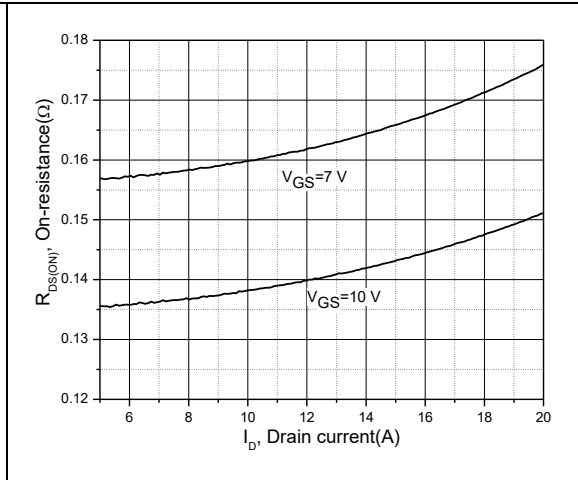


Figure 8, Drain-source on-state resistance

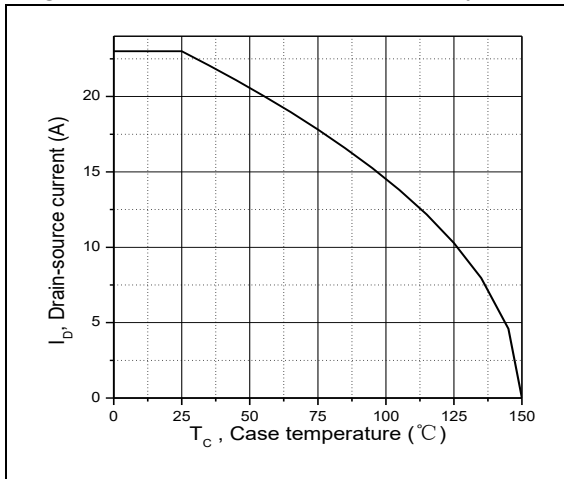


Figure 9, Drain current

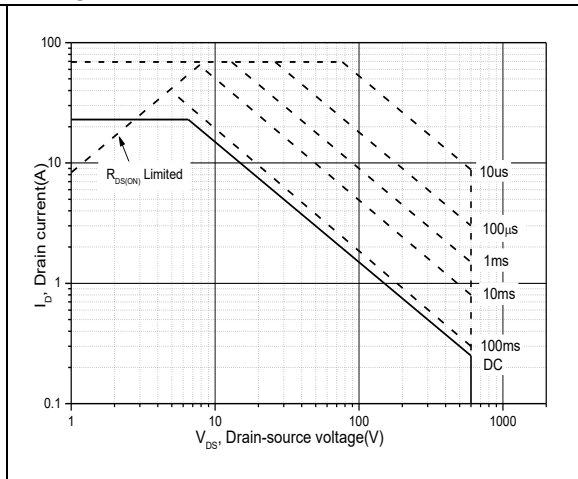


Figure 10, Safe operation area $T_C=25\text{ }^\circ\text{C}$

■ Test circuits and waveforms

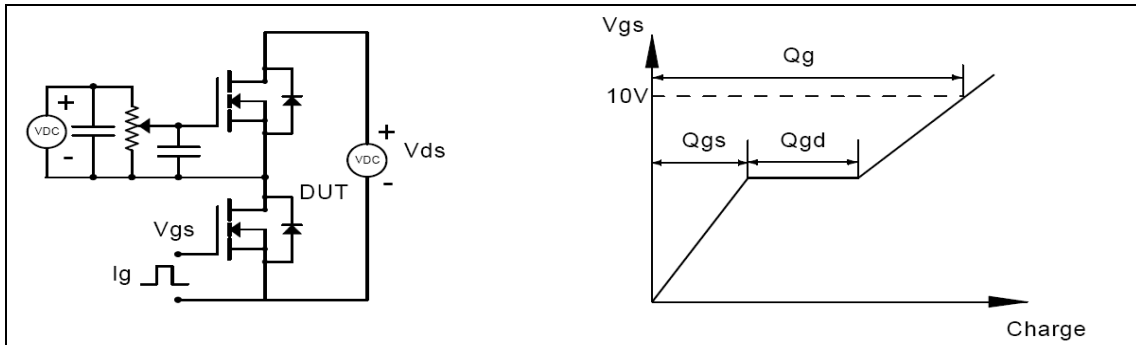


Figure 1, Gate charge test circuit & waveform

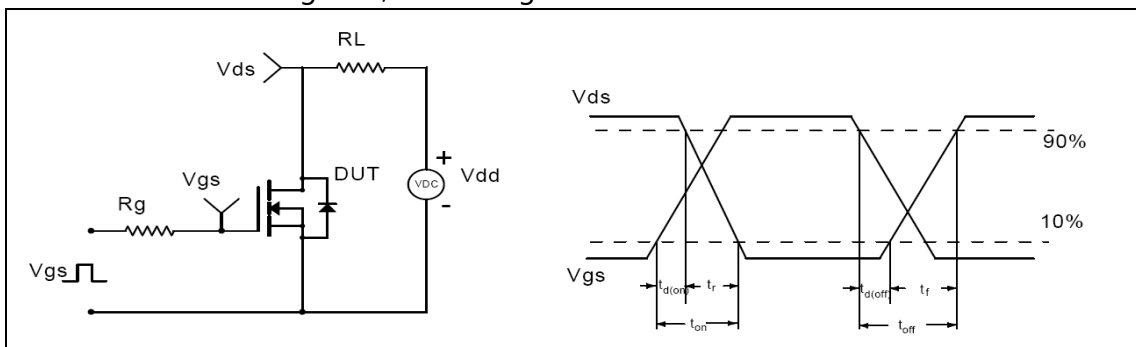


Figure 2, Switching time test circuit & waveforms

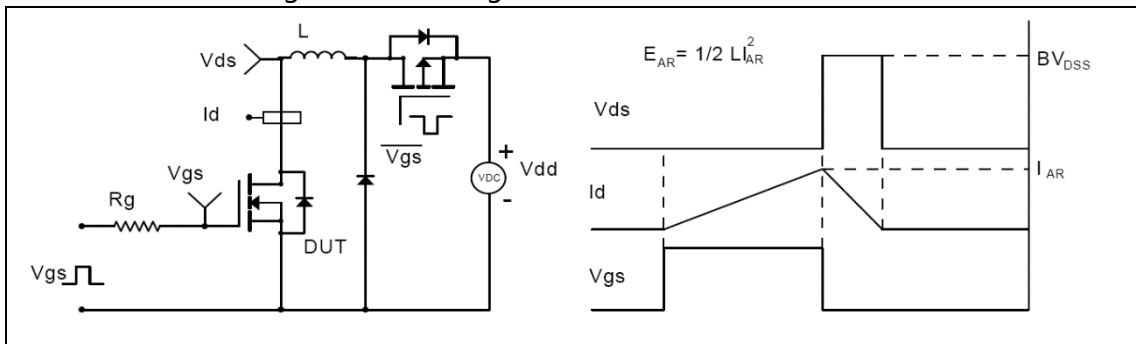


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

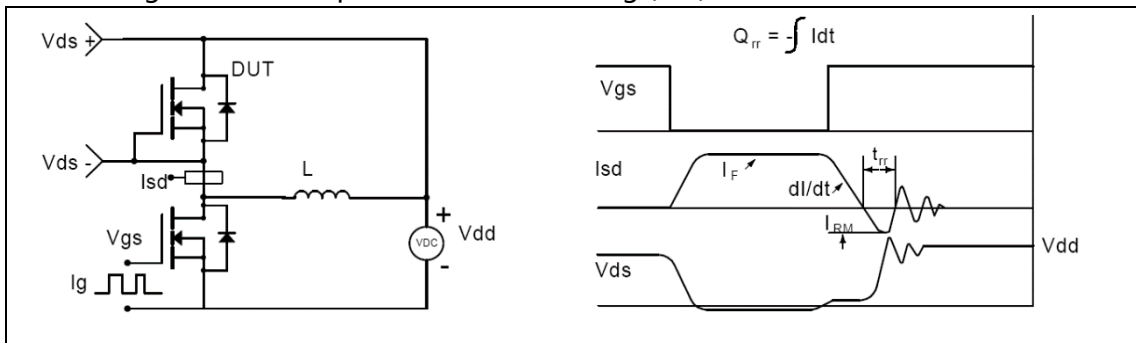
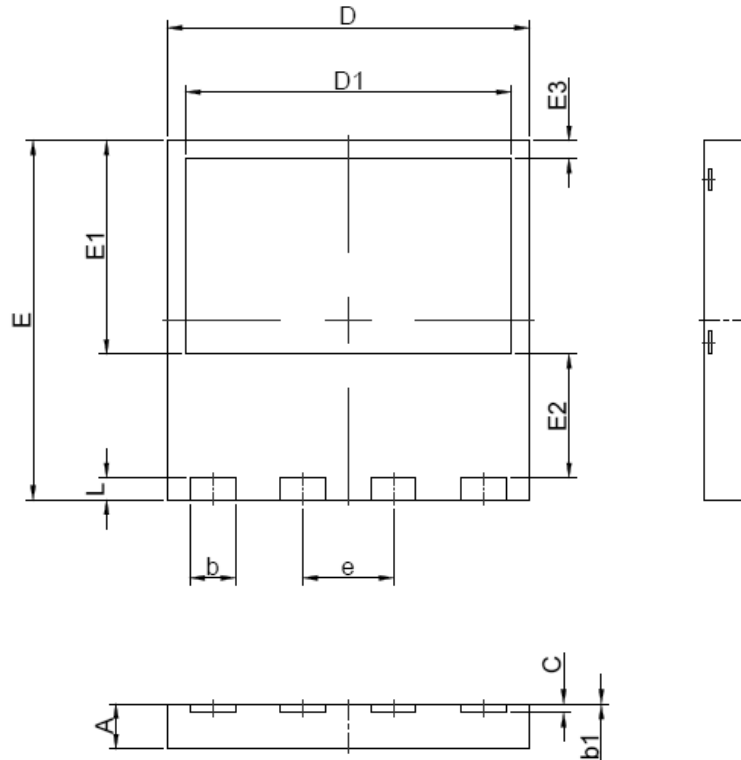


Figure 4, Diode reverse recovery test circuit & waveforms

■ Package Information

Figure1, PDFN8×8 package outline dimension



DIM	MIN	MAX	TYP
A	0.90	1.10	1.00
b	0.90	1.10	1.00
b1	0.00	0.05	0.02
C	0.2 REF		
D	7.90	8.10	8.00
D1	7.10	7.30	7.20
E	7.90	8.10	8.00
E1	4.65	4.85	4.75
E2	2.65	2.85	2.75
E3	0.30	0.50	0.40
e	2.0 BSC		
L	0.40	0.60	0.50

■ Ordering Information

Package	Units/Tape	Tubes/Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
PDFN8×8	2500	2	5000	5	25000

■ Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG60R150JF	PDFN8×8	yes	yes	yes